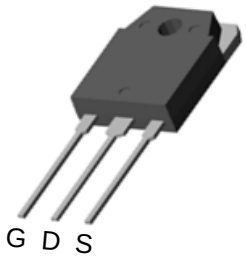
FIR10N80ANG

N-Channel Power MOSFET

V_{DSS}	800	V
I_D	9	A
$P_D(T_C=25℃)$	190	W
$R_{DS(ON)}$	0.9	Ω

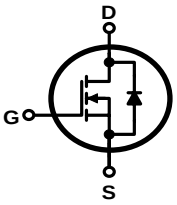
PIN Connection TO-3P



Features

- **Fast Switching**
- **Low ON Resistance(Rdson≤1. 25Ω)**
- **Low Gate Charge (Typical Data: 48nC)**
- **Low Reverse transfer capacitances(Typical: 17pF)**
- **100% Single Pulse avalanche energy Test**

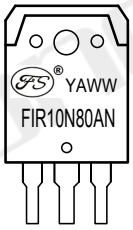
Schematic diagram



Applications

Power switch circuit of adaptor and charger

Marking Diagram



Y = Year
A = Assembly Location
WW = Work Week
FIR10N80AN = Specific Device Code

Absolute（Tc= 25℃ unless otherwise specified）:

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	800	V
I_D	Continuous Drain Current	9	A
	Continuous Drain Current T_C = 100 °C	5.4	A
I_{DM} [a1]	Pulsed Drain Current	36	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS} [a2]	Single Pulse Avalanche Energy	950	mJ
E_{AR} [a1]	Avalanche Energy ,Repetitive	85	mJ
I_{AR} [a1]	Avalanche Current	13.8	A
dv/dt [a3]	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	190	W
	Derating Factor above 25°C	1.52	W/℃
T_J， T_{stg}	Operating Junction and Storage Temperature Range	150，–55 to 150	℃
T_L	MaximumTemperature for Soldering	300	℃

Electrical Characteristics（Tc= 25℃ unless otherwise specified）：

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	800	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	ID=250uA,Reference25℃	--	0.85	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS} = 800V, V_{GS}= 0V, T_a = 25℃	--	--	10	μA
		V_{DS} =640V, V_{GS}= 0V, T_a = 125℃	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+30V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V,I_D=4.0A	--	0.9	1.2	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	3.0	3.5	4.5	V
Pulse width tp≤380μs, δ ≤2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	V_{DS}=15V, I_D =4A	--	8.5	--	S
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1.0MHz	--	2400	--	pF
C_{oss}	Output Capacitance		--	160	--	
C_{rss}	Reverse Transfer Capacitance		--	17	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =8.0A V_{DD} =400V V_{GS} = 10V R_G = 25Ω	--	40	--	ns
tr	Rise Time		--	120	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	70	--	
t_f	Fall Time		--	80	--	
Q_g	Total Gate Charge	I_D =8.0A V_{DD} =480V V_{GS} = 10V	--	48	60	nC
Q_{gs}	Gate to Source Charge		--	11	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	16	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	9	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	36	A
V_{SD}	Diode Forward Voltage	I_S=8.0A,V_{GS}=0V	--	--	1.5	V
trr	Reverse Recovery Time	I_S=8.0A,T_j = 25° C dI_F/dt=100A/us, V_{GS}=0V	--	570	--	ns
Qrr	Reverse Recovery Charge		--	8130	--	nC
I_{RRM}	Reverse Recovery Current		--	18	--	A
Pulse width tp≤380μs, δ ≤2%						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	0.66	℃/W
$R_{\theta JA}$	Junction-to-Ambient	62.5	℃/W

[a1]: Repetitive rating; pulse width limited by maximum junction temperature
[a2]: L=10.0mH, I_D=8A, Start T_J=25℃
[a3]: I_{SD} =8A,di/dt ≤100A/us,V_{DD}≤$BV_{DS,}$ Start T_J=25℃

Characteristics Curves

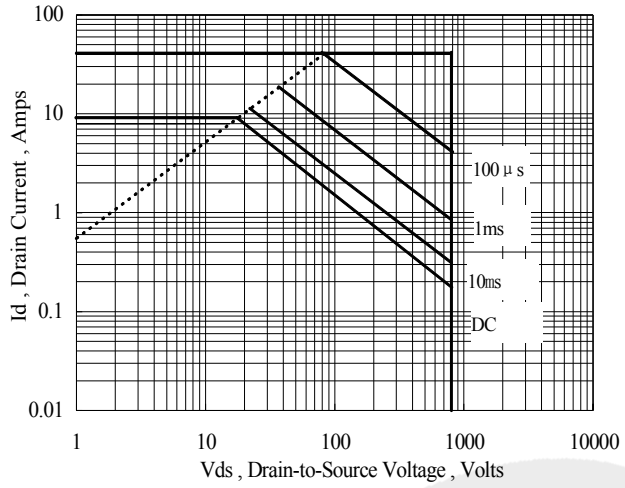


Figure 1 Maximun Forward Bias Safe Operating Area

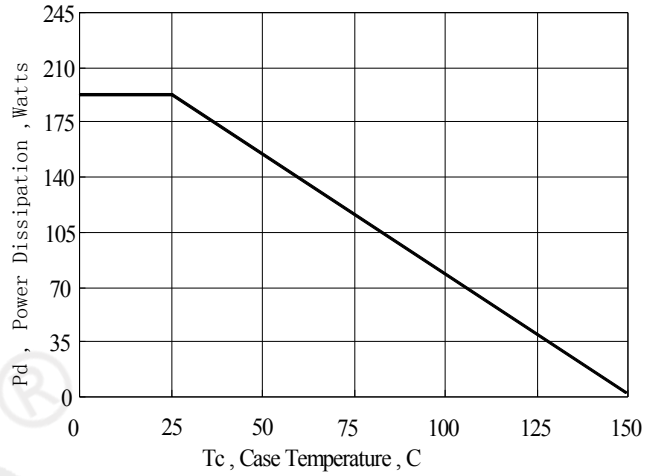


Figure 2 Maximun Power Dissipation vs Case Temperature

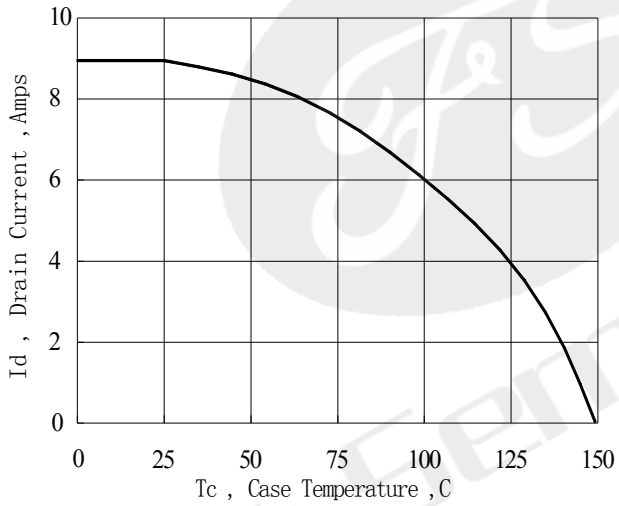


Figure 3 Maximum Continuous Drain Current vs Case Temperature

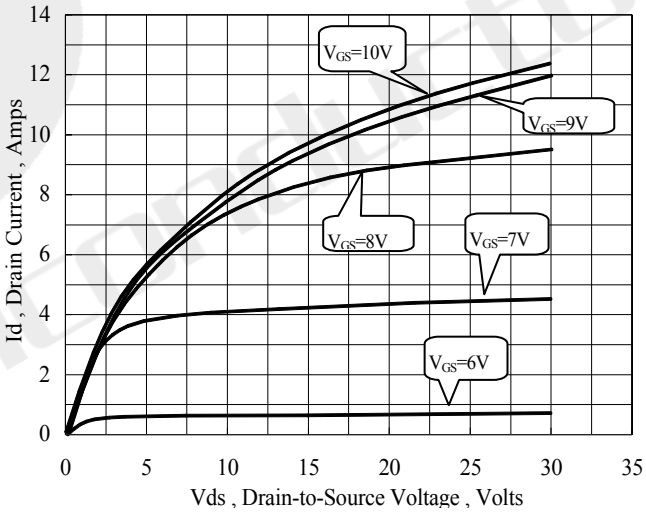


Figure 4 Typical Output Characteristics

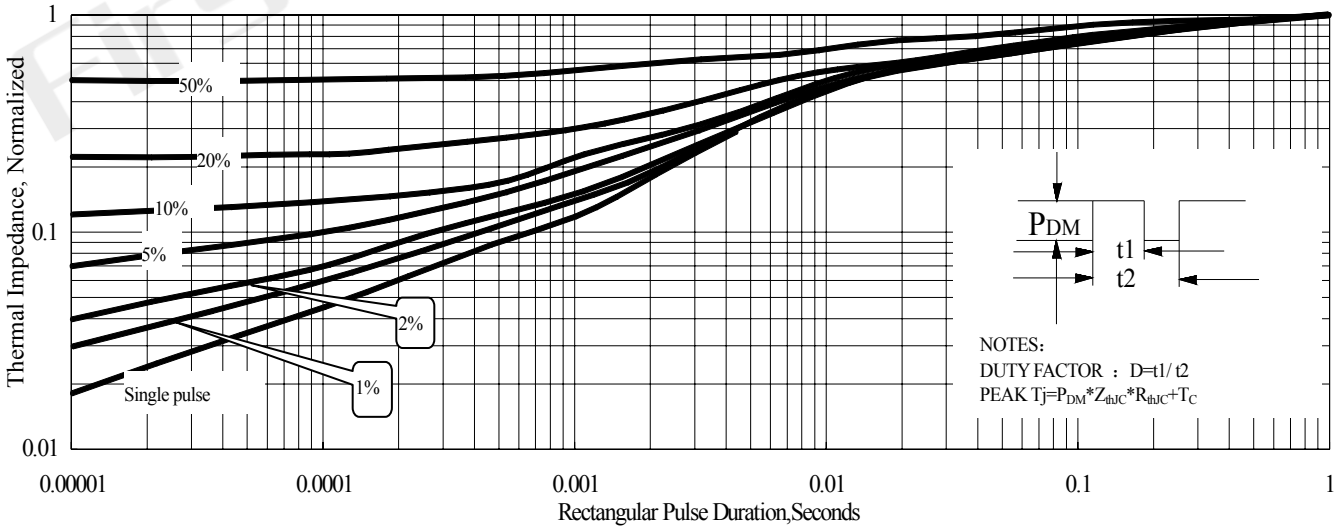


Figure 5 Maximum Effective Thermal Impendance , Junction to Case

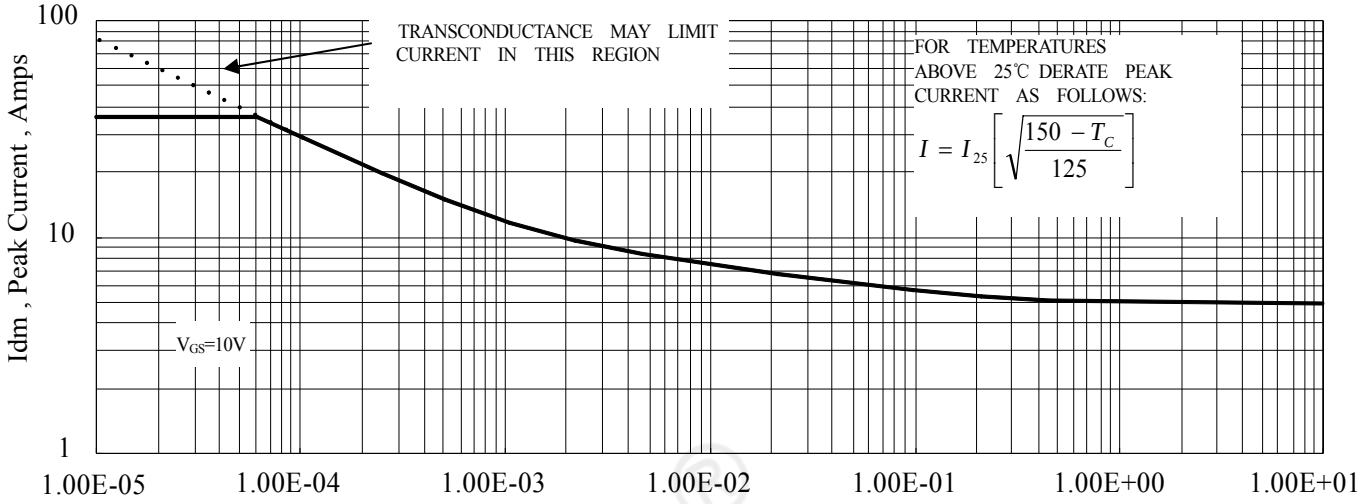


Figure 6 Maximum Peak Current Capability

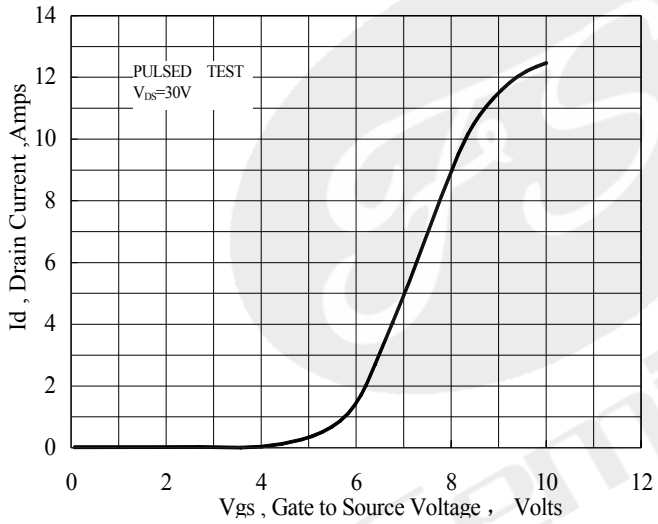


Figure 7 Typical Transfer Characteristics

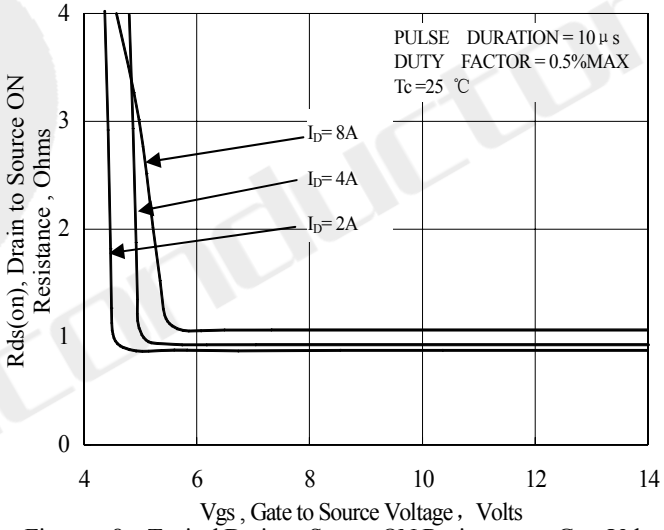


Figure 8 Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current

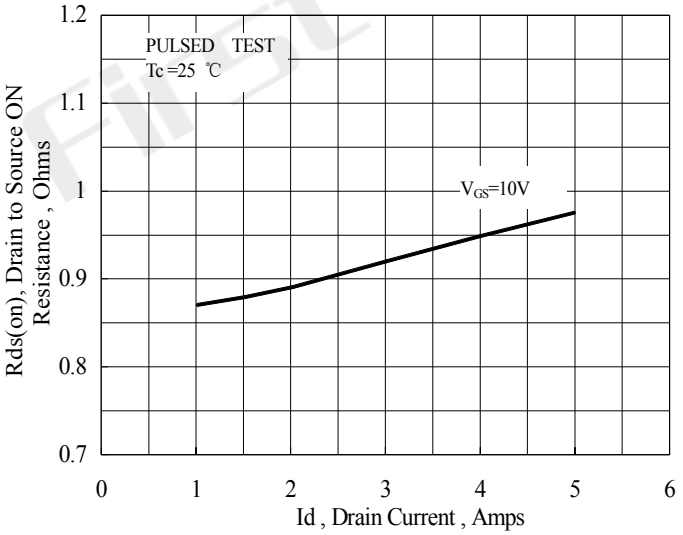


Figure 9 Typical Drain to Source ON Resistance vs Drain Current

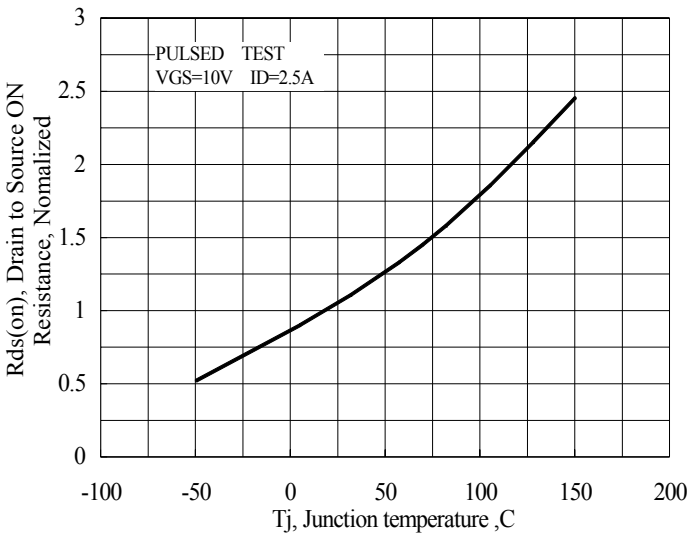


Figure 10 Typical Drian to Source on Resistance vs Junction Temperature

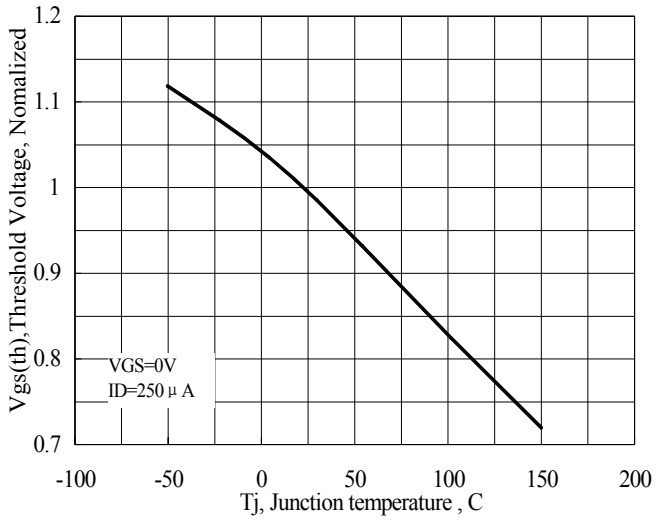


Figure 11 Typical Theshold Voltage vs Junction Temperature

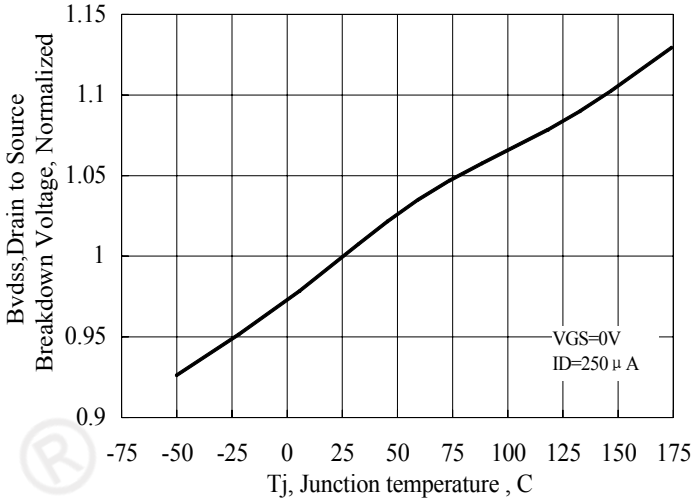


Figure 12 Typical Breakdown Voltage vs Junction Temperature

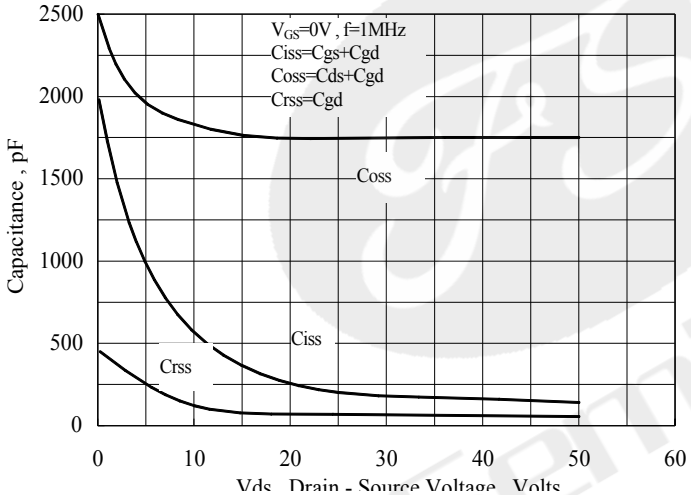


Figure 13 Typical Capacitance vs Drain to Source Voltage

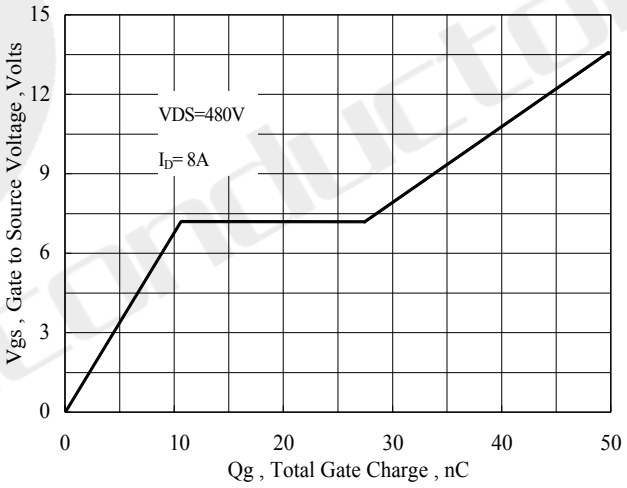


Figure 14 Typical Gate Charge vs Gate to Source Voltage

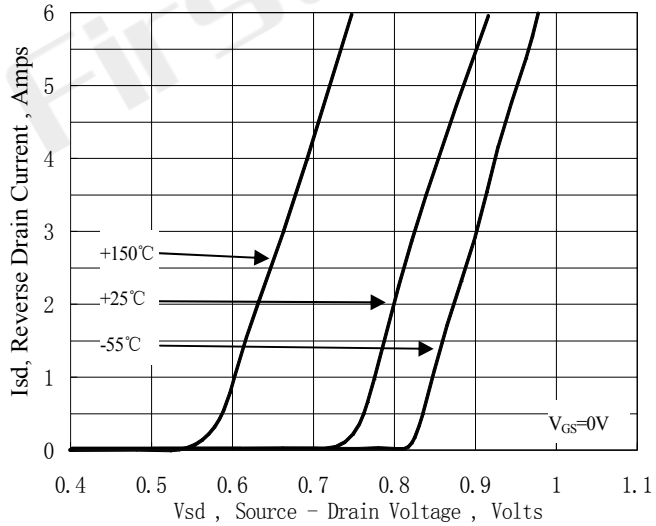


Figure 15 Typical Body Diode Transfer Characteristics

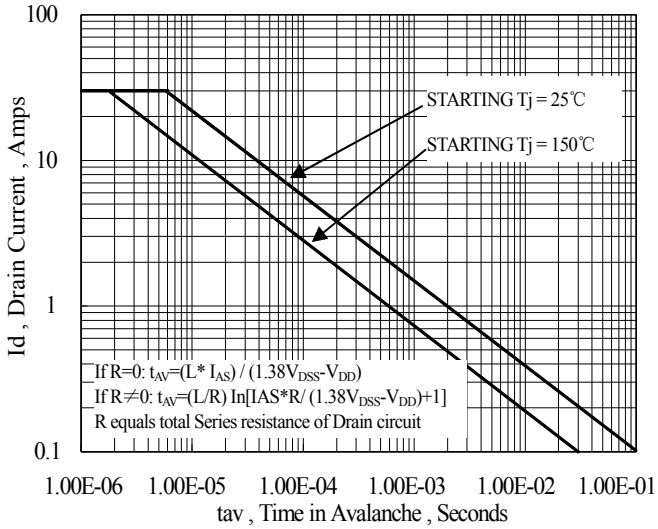
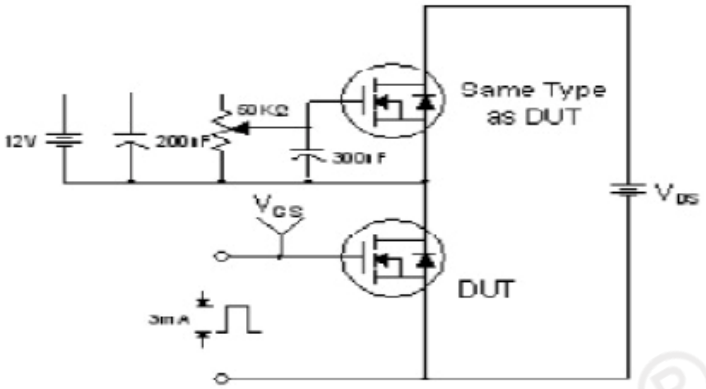
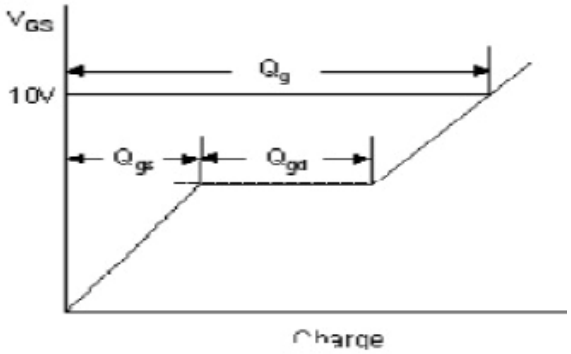


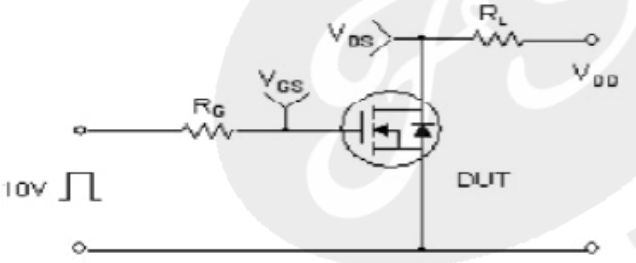
Figure 16 Unclamped Inductive Switching Capability

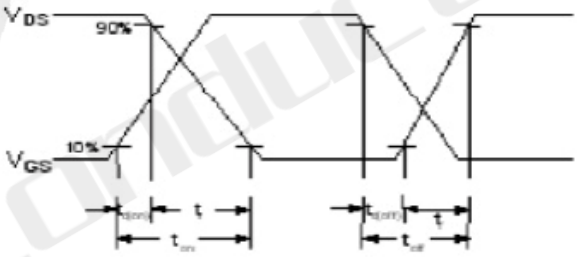
Test Circuitand Waveform



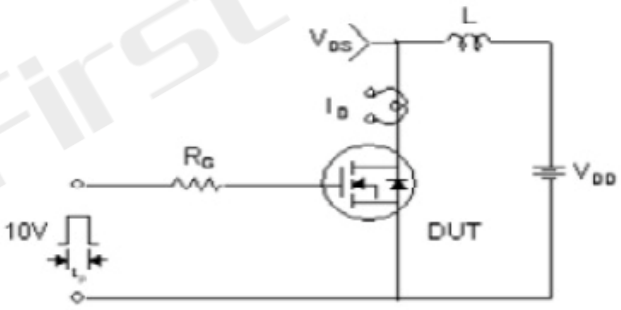


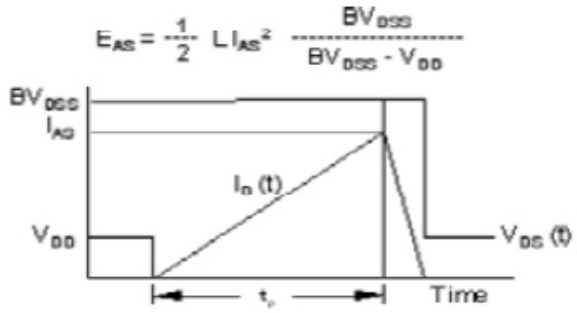
Gate Charge Test Circuit and Waveform



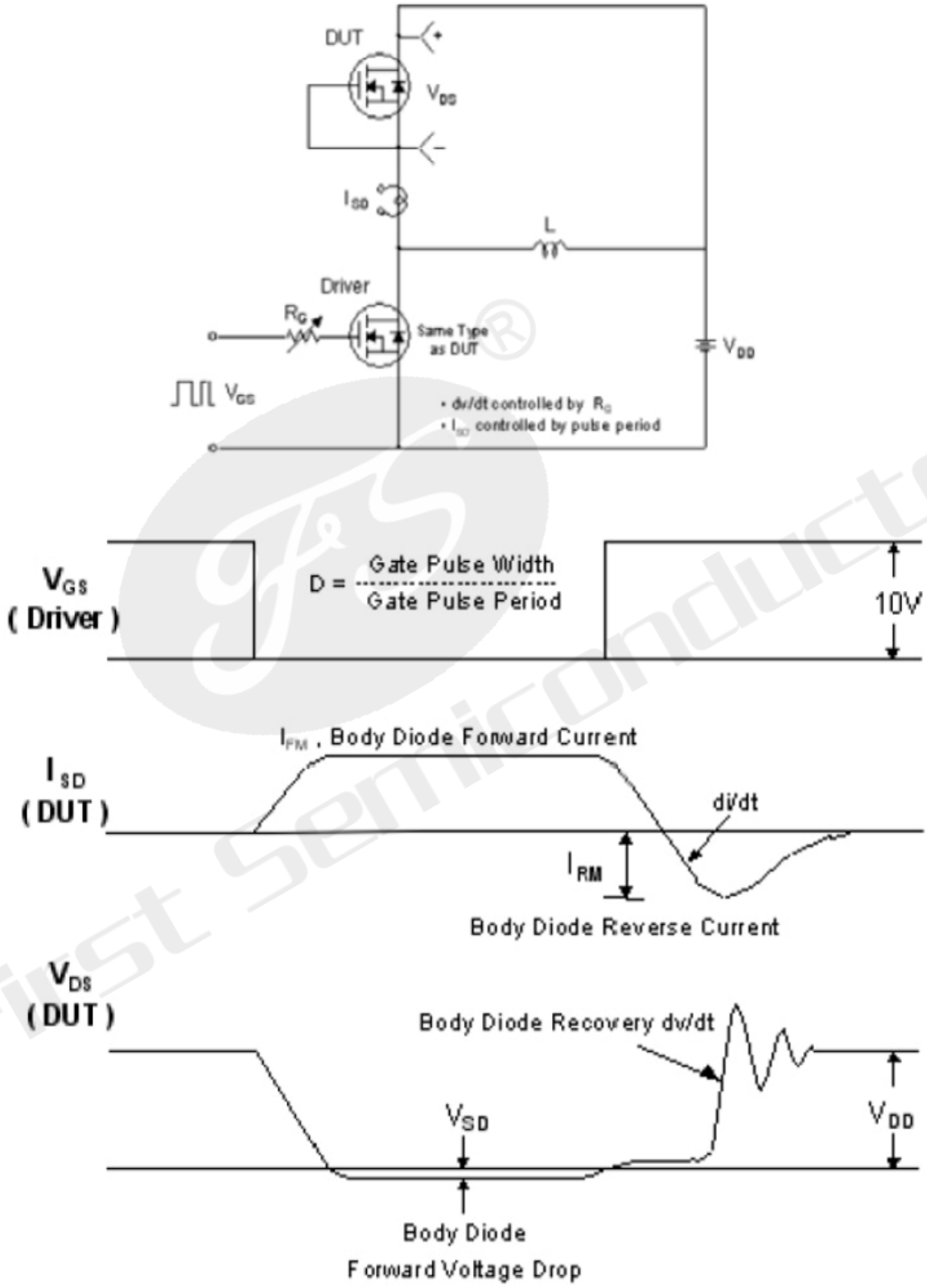


Resistive Switching Test Circuit and Waveform

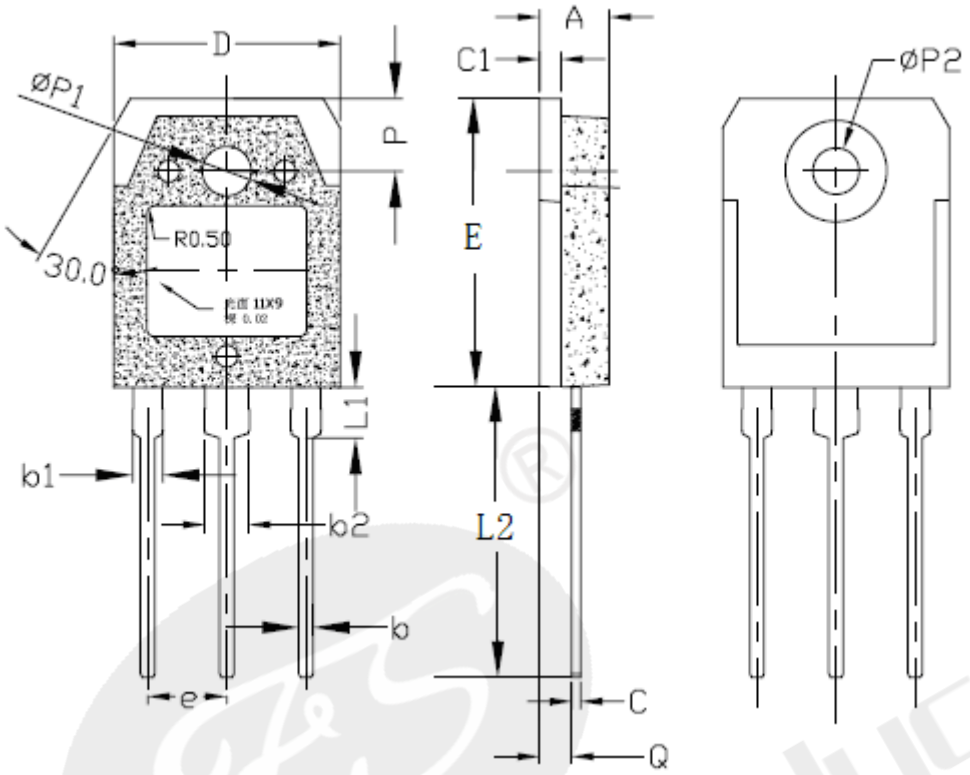




Unclamped Inductive Switching Test Circuit and Waveform



Diode Reverse Recovery Test Circuit and Waveform



Units: mm

TO-3P Dimensions					
SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.181	0.197	4.60	5.00	
b	0.031	0.047	0.80	1.20	
b1	0.071	0.087	1.80	2.20	
b2	0.110	0.126	2.80	3.20	
c	0.022	0.030	0.55	0.75	
c1	0.057	0.065	1.45	1.65	
D	0.606	0.622	15.40	15.80	
E	0.776	0.791	19.70	20.10	
e	0.215 TYP		5.45 TYP		
L1	0.126MAX.		3.2 MAX.		
L2	0.780	0.795	19.80	20.20	
P	0.197	0.213	5.0	5.4	
ΦP1	0.130	0.138	3.30	3.50	
ΦP2	（0.126）		（3.20）		
Q	0.087	0.102	2.20	2.60	

Declaration

- FIRST reserves the right to change the specifications, the same specifications of products due to different packaging line mold, the size of the appearance will be slightly different, shipped in kind, without notice! Customers should obtain the latest version information before ordering, and verify whether the relevant information is complete and up-to-date.
- Any semiconductor product under certain conditions has the possibility of failure or failure,The buyer has the responsibility to comply with safety standards and take safety measures when using FIRST products for system design and manufacturing,To avoid To avoid potential failure risks, which may cause personal injury or property damage!
- Product promotion endless, our company will wholeheartedly provide customers with better products!

ATTACHMENT

Revision History

Date	REV	Description	Page
2018.01.01	1.0	Initial release	